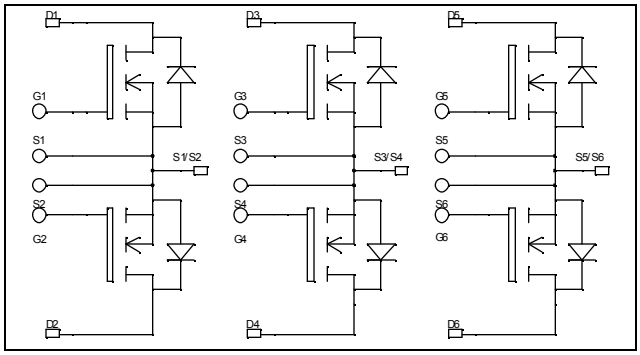
APTM120TDU57P

Triple dual common source MOSFET Power Module

V_{DSS} = 1200V
R_{DSon} = 570mΩ max @ Tj = 25°C
I_D = 17A @ Tc = 25°C

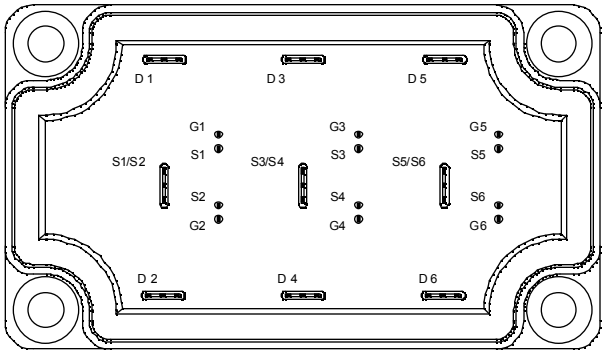


Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7® MOSFETs
  - Low R_{DSon}
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- High level of integration



Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Very low (12mm) profile
- Each leg can be easily paralleled to achieve a dual common source configuration of three times the current capability

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{DSS}	Drain - Source Breakdown Voltage		1200	V
I_D	Continuous Drain Current	T_c = 25°C	17	A
		T_c = 80°C	13	
I_{DM}	Pulsed Drain current		68	
V_{GS}	Gate - Source Voltage		±30	V
R_{DSon}	Drain - Source ON Resistance		570	mΩ
P_D	Maximum Power Dissipation	T_c = 25°C	390	W
I_{AR}	Avalanche current (repetitive and non repetitive)		22	A
E_{AR}	Repetitive Avalanche Energy		50	mJ
E_{AS}	Single Pulse Avalanche Energy		3000	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed.

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
BV_{DSS}	Drain - Source Breakdown Voltage	V_{GS} = 0V, I_D = 250µA		1200			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V, V_{DS} = 1200V	T_j = 25°C			100	µA
		V_{GS} = 0V, V_{DS} = 1000V	T_j = 125°C			500	
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 8.5A				570	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 2.5mA		3		5	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±30 V, V_{DS} = 0V				±100	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*	*Min*	*Typ*	*Max*	*Unit*
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1MHz		5155		pF
C_{oss}	Output Capacitance			770		
C_{rss}	Reverse Transfer Capacitance			130		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 600V I_D = 17A		187		nC
Q_{gs}	Gate – Source Charge			24		
Q_{gd}	Gate – Drain Charge			120		
$T_{d(on)}$	Turn-on Delay Time	**Inductive switching @ 125°C** V_{GS} = 15V V_{Bus} = 800V I_D = 17A R_G = 5Ω		20		ns
T_r	Rise Time			15		
$T_{d(off)}$	Turn-off Delay Time			160		
T_f	Fall Time			45		
E_{on}	Turn-on Switching Energy ❶	**Inductive switching @ 25°C** V_{GS} = 15V, V_{Bus} = 800V I_D = 17A, R_G = 5Ω		990		µJ
E_{off}	Turn-off Switching Energy ❷			685		
E_{on}	Turn-on Switching Energy ❶	**Inductive switching @ 125°C** V_{GS} = 15V, V_{Bus} = 800V I_D = 17A, R_G = 5Ω		1565		µJ
E_{off}	Turn-off Switching Energy ❷			857		

Source - Drain diode ratings and characteristics

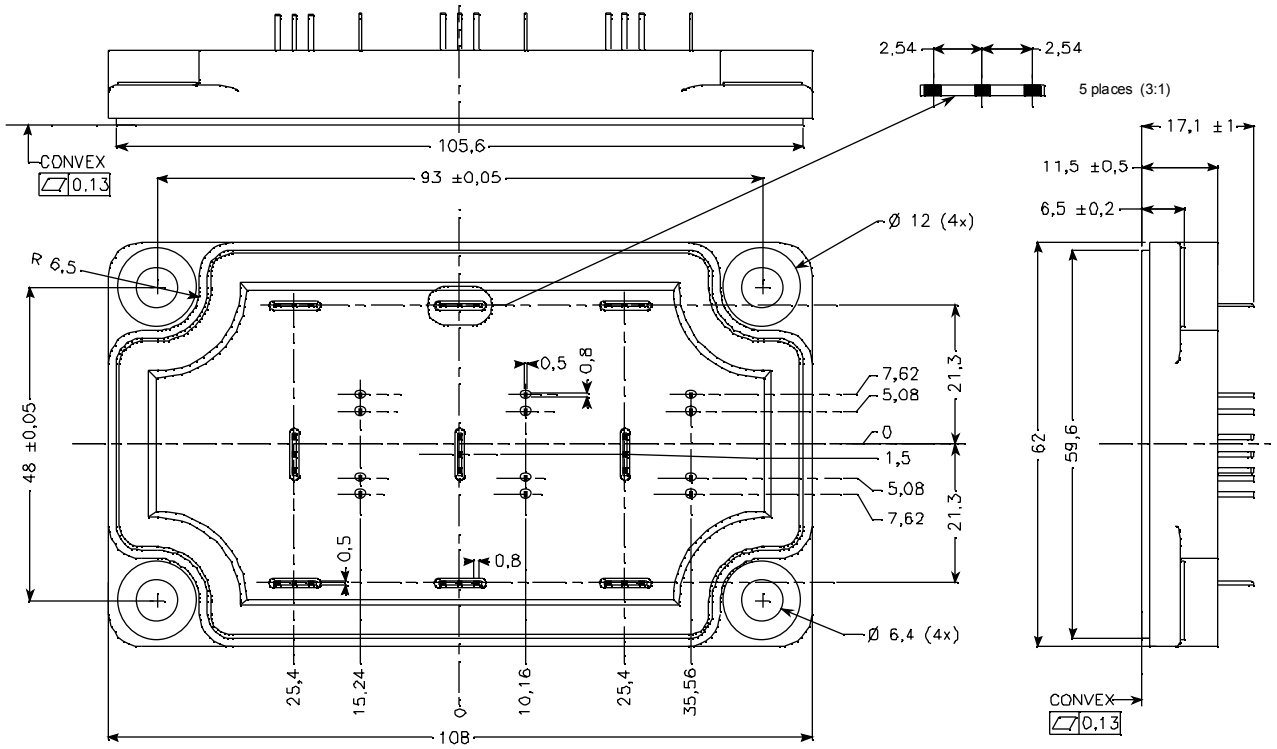
Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_S	Continuous Source current (Body diode)		Tc = 25°C			17	A
			Tc = 80°C			13	
V_{SD}	Diode Forward Voltage	V_{GS} = 0V, I_S = - 17A				1.3	V
dv/dt	Peak Diode Recovery ❸					10	V/ns
t_{rr}	Reverse Recovery Time	I_S = - 17A V_R = 600V di_S/dt = 100A/µs	T_j = 25°C		1291		ns
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		29		µC

❶ E_{on} includes diode reverse recovery.
❷ In accordance with JEDEC standard JESD24-1.
❸ dv/dt numbers reflect the limitations of the circuit rather than the device itself.
$I_S \le$ - 17A di/dt ≤ 700A/µs $V_R \le V_{DSS}$ $T_j \le$ 150°C

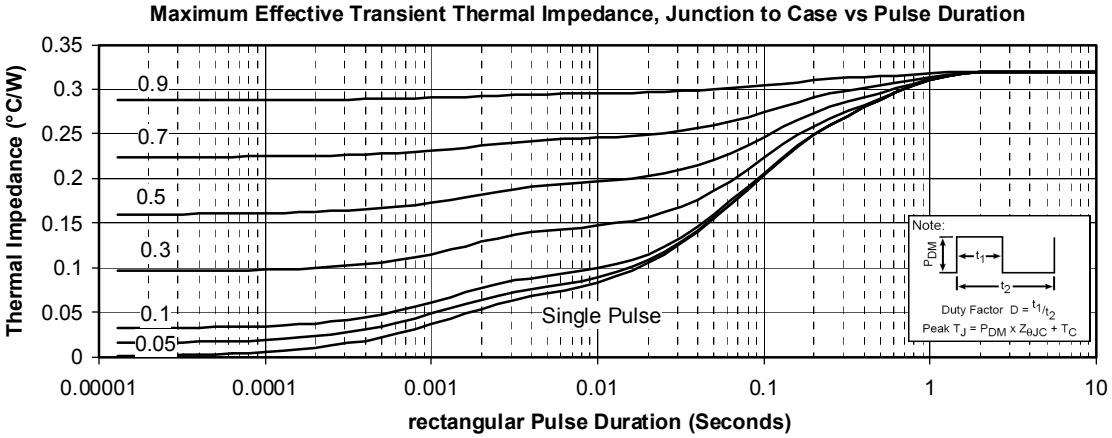
Thermal and package characteristics

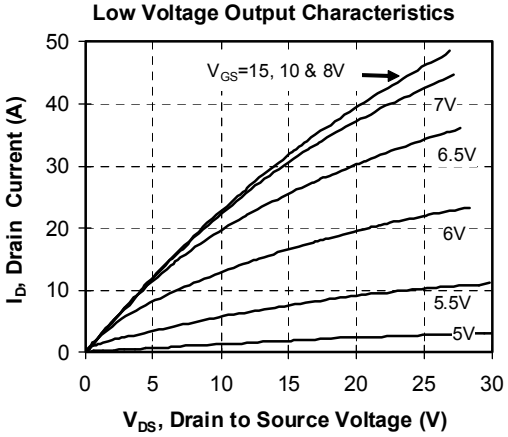
Symbol	*Characteristic*			*Min*	*Typ*	*Max*	*Unit*
R_{thJC}	Junction to Case		IGBT			0.32	°C/W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Wt	Package Weight					250	g

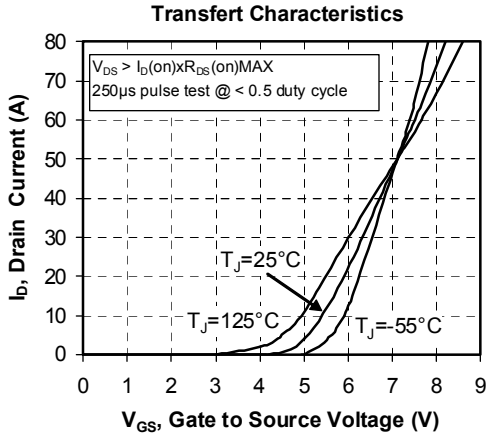
Package outline

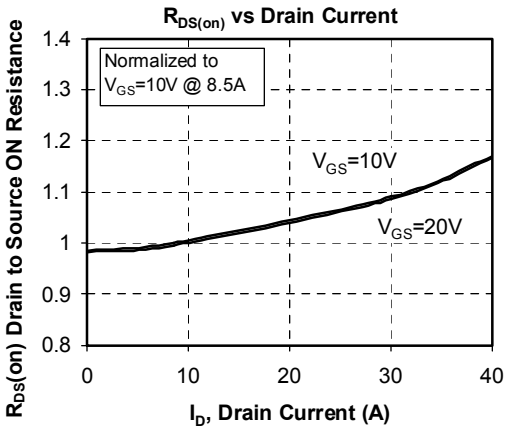


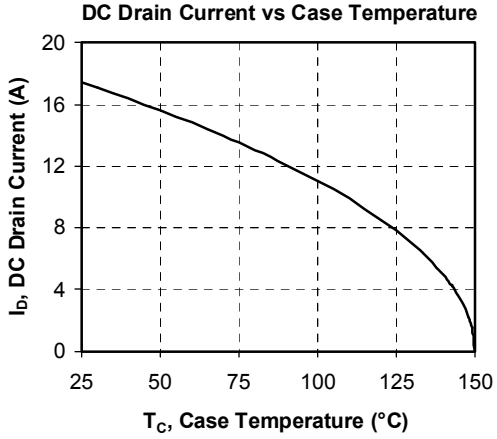
Typical Performance Curve



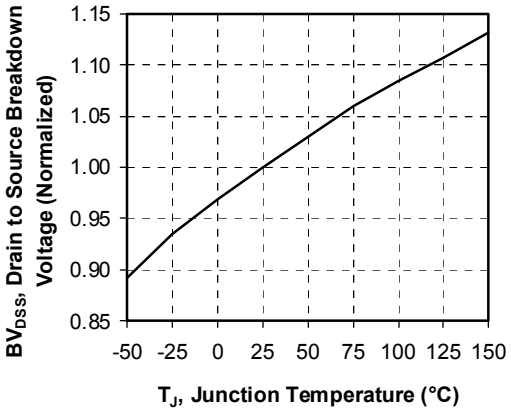




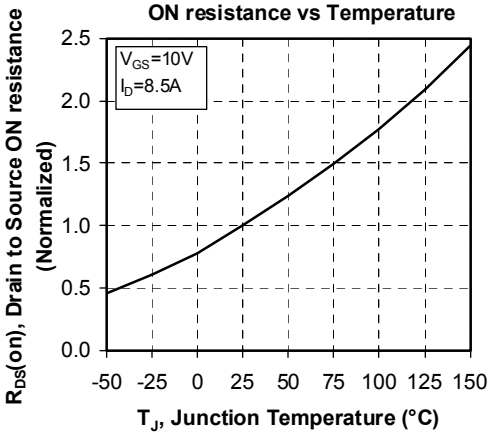




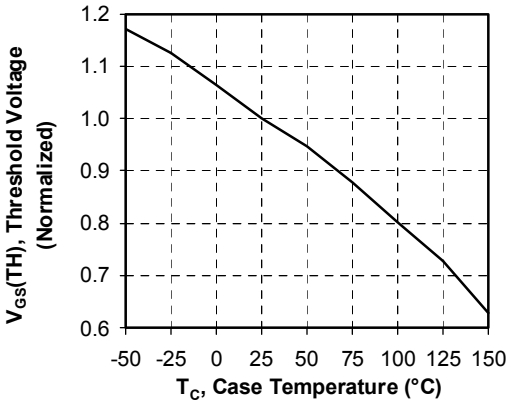
Breakdown Voltage vs Temperature



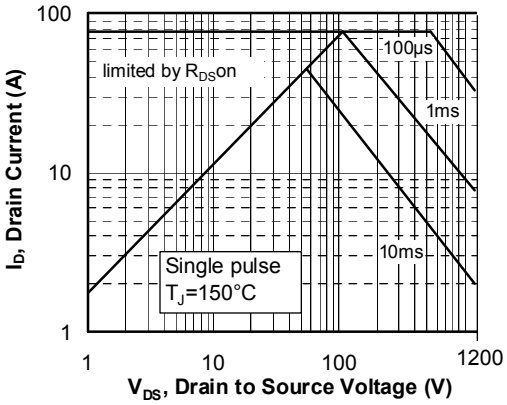
ON resistance vs Temperature



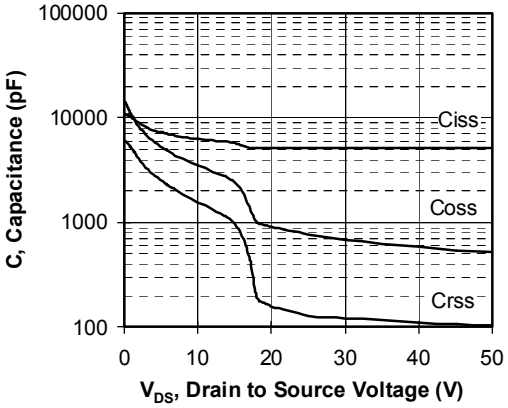
Threshold Voltage vs Temperature



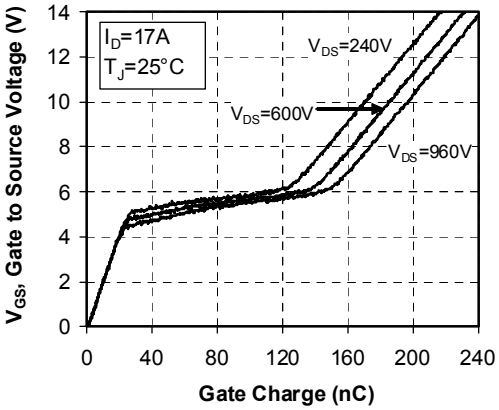
Maximum Safe Operating Area



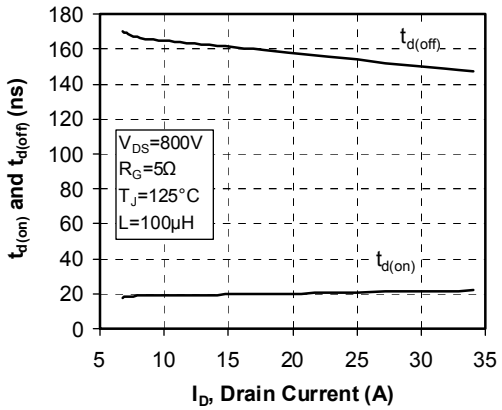
Capacitance vs Drain to Source Voltage



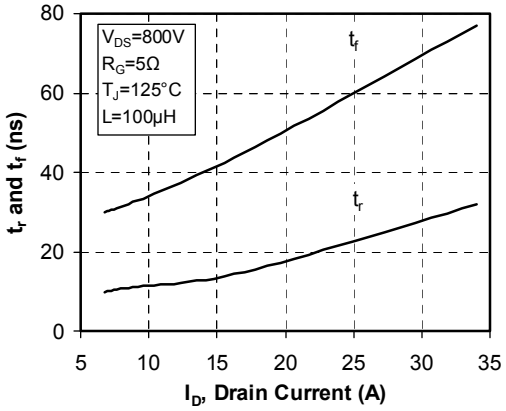
Gate Charge vs Gate to Source Voltage



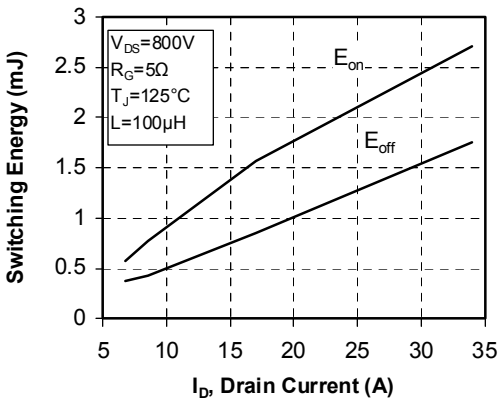
Delay Times vs Current



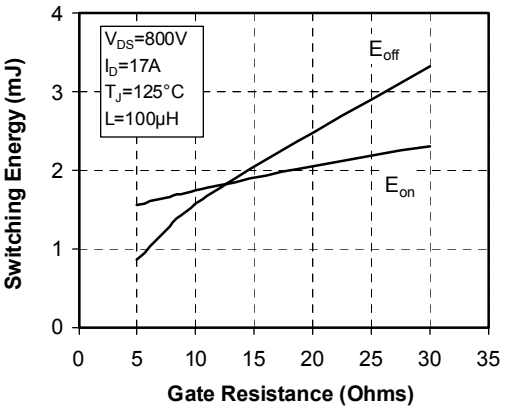
Rise and Fall times vs Current



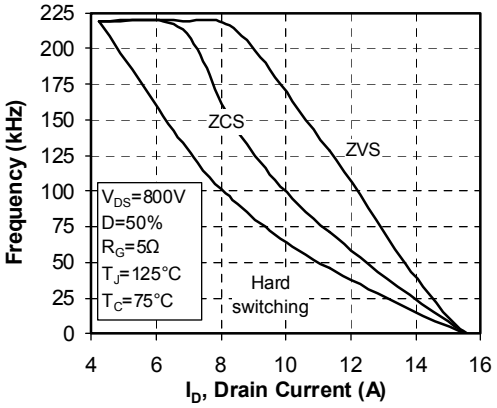
Switching Energy vs Current



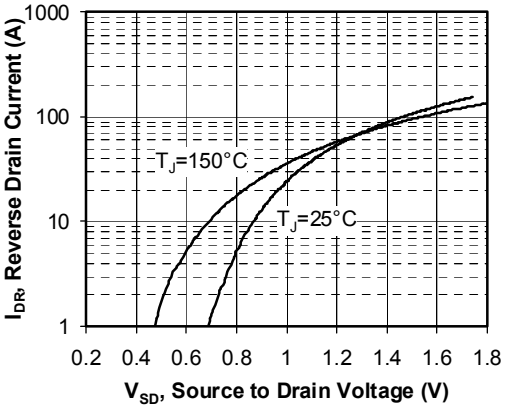
Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage



APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.